



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

INOUE

Atty. Ref.: 900-379

Serial No. 09/826,833

Group: 2823

Filed: April 6, 2001

Examiner: Estrada, M.

For: METHOD FOR PRODUCING SEMICONDUCTOR DEVICE

* * * * *

December 11, 2002

Assistant Commissioner for Patents
Washington, DC 20231

Sir:

AMENDMENT AFTER FINAL

Responsive to the Official Action dated September 12, 2002, please amend the above-identified application as follows:

IN THE CLAIMS

Please cancel claims 10-11.

Please substitute the following amended claim(s) for corresponding claim(s) previously presented. A copy of the amended claim(s) showing current revisions is attached.

1. (Amended) A method for producing a semiconductor device comprising:

forming a resist pattern to be used as a mask over a multi-layered film, wherein the multi-layered film includes a nitride etching stop film, a first organic insulating film, a first oxide etching stop film, a second organic insulating film, and a second oxide etching

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